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Serial no. 10/047,266

Attorney docket no. 67,200-641

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In the Claims

1. - 3. (cancelled)

4. (currently amended) The method of claim + 11, wherein plasma curing the at least one photoresist layer increases ion dosage of the at least one photoresist layer.

5.-7. (cancelled)

8. (currently amended) The method of claim + 11, wherein measuring the one or more critical dimensions using the electron beam comprises critical dimension scanning electron microscope measurement of the one or more critical dimensions.

9. (currently amended) The method of claim + 11, wherein measuring the one or more critical dimensions using the electron beam comprises after-development inspection of the one or more critical dimensions.

10. (currently amended) The method of claim + 11, wherein measuring the one or more critical dimensions using the electron beam comprises after-etching inspection of the one or more critical dimensions.

11. (previously presented) A method comprising:  
plasma curing a semiconductor wafer having at least one photoresist layer; and,  
after plasma curing the semiconductor wafer, measuring one or more critical dimensions on the at least one photoresist layer using an electron beam,  
such that plasma curing the semiconductor wafer prior to measuring the one or more critical dimensions using the electron beam substantially reducing shrinkage of the at least one photoresist layer when using the electron beam.

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12. (previously presented) The method of claim 11, wherein plasma curing the semiconductor wafer increases ion dosage of the at least one photoresist layer, increasing resistance of the at least one photoresist layer to shrinkage when using the electron beam.

13.-14. (cancelled)

15. (previously presented) The method of claim 11, wherein measuring the one or more critical dimensions using the electron beam comprises one of: critical dimension scanning electron microscope measurement of the one or more critical dimensions; after-development inspection of the one or more critical dimensions; and, after-etching inspection of the one or more critical dimensions.

16. - 20. (cancelled)